

## Excellent Integrated System Limited

Stocking Distributor

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[IXYS Corporation](#)  
[VUO55-16NO7](#)

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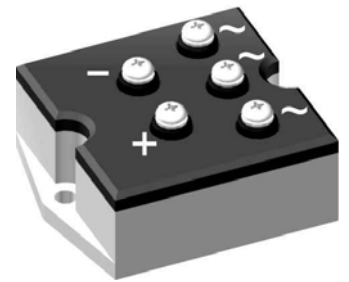
## Standard Rectifier Module


<b>3~ Rectifier</b>	
$V_{RRM}$	= 1600 V
$I_{DAV}$	= 60 A
$I_{FSM}$	= 750 A

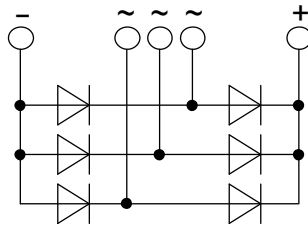
### 3~ Rectifier Bridge

Part number

**VUO55-16N07**



 E72873



#### Features / Advantages:

- Package with DCB ceramic
- Improved temperature and power cycling
- Planar passivated chips
- Very low forward voltage drop
- Very low leakage current

#### Applications:

- Diode for main rectification
- For three phase bridge configurations
- Supplies for DC power equipment
- Input rectifiers for PWM inverter
- Battery DC power supplies
- Field supply for DC motors

#### Package: PWS-B

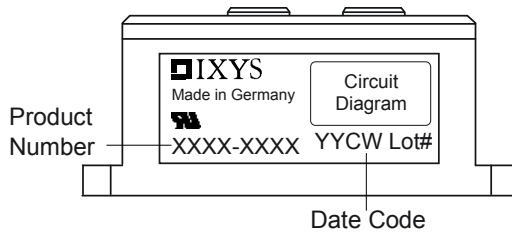
- Industry standard outline
- RoHS compliant
- Easy to mount with two screws
- Base plate: Aluminium internally DCB isolated
- Advanced power cycling

Rectifier				Ratings			
Symbol	Definition	Conditions	min.	typ.	max.	Unit	
$V_{RSM}$	max. non-repetitive reverse blocking voltage				1700	V	
$V_{RRM}$	max. repetitive reverse blocking voltage				1600	V	
$I_R$	reverse current	$V_R = 1600\text{ V}$	$T_{VJ} = 25^\circ\text{C}$		100	$\mu\text{A}$	
		$V_R = 1600\text{ V}$	$T_{VJ} = 150^\circ\text{C}$		1.5	mA	
$V_F$	forward voltage drop	$I_F = 20\text{ A}$	$T_{VJ} = 25^\circ\text{C}$		1.03	V	
					1.23	V	
		$I_F = 60\text{ A}$	$T_{VJ} = 125^\circ\text{C}$		0.92	V	
					1.18	V	
$I_{DAV}$	bridge output current	$T_C = 85^\circ\text{C}$ rectangular $d = 1/3$	$T_{VJ} = 150^\circ\text{C}$		60	A	
$V_{F0}$	threshold voltage	} for power loss calculation only	$T_{VJ} = 150^\circ\text{C}$		0.76	V	
$r_F$	slope resistance				6.9	m $\Omega$	
$R_{thJC}$	thermal resistance junction to case				2.7	K/W	
$R_{thCH}$	thermal resistance case to heatsink			0.4		K/W	
$P_{tot}$	total power dissipation		$T_C = 25^\circ\text{C}$		46	W	
$I_{FSM}$	max. forward surge current	$t = 10\text{ ms}; (50\text{ Hz}), \text{ sine}$	$T_{VJ} = 45^\circ\text{C}$		750	A	
					810	A	
		$t = 8,3\text{ ms}; (60\text{ Hz}), \text{ sine}$	$V_R = 0\text{ V}$	$T_{VJ} = 150^\circ\text{C}$		640	A
						690	A
$I^2t$	value for fusing	$t = 10\text{ ms}; (50\text{ Hz}), \text{ sine}$	$T_{VJ} = 45^\circ\text{C}$		2.82	kA <sup>2</sup> s	
					2.73	kA <sup>2</sup> s	
		$t = 8,3\text{ ms}; (60\text{ Hz}), \text{ sine}$	$V_R = 0\text{ V}$	$T_{VJ} = 150^\circ\text{C}$		2.05	kA <sup>2</sup> s
						1.98	kA <sup>2</sup> s
$C_J$	junction capacitance	$V_R = 400\text{ V}; f = 1\text{ MHz}$	$T_{VJ} = 25^\circ\text{C}$	10		pF	



# VUO55-16NO7

Package PWS-B		Ratings				
Symbol	Definition	Conditions	min.	typ.	max.	Unit
$I_{RMS}$	RMS current	per terminal			100	A
$T_{stg}$	storage temperature		-40		125	°C
$T_{vj}$	virtual junction temperature		-40		150	°C
<b>Weight</b>				203		g
$M_D$	mounting torque		4.25		5.75	Nm
$M_T$	terminal torque		2.5		3.5	Nm
$d_{Spp/App}$	creepage distance on surface   striking distance through air	terminal to terminal	11.0			mm
$d_{Spb/Apb}$		terminal to backside	7.5			mm
$V_{ISOL}$	isolation voltage	t = 1 second	3000			V
		t = 1 minute	2500			V



Ordering	Part Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	VUO55-16NO7	VUO55-16NO7	Box	10	456691

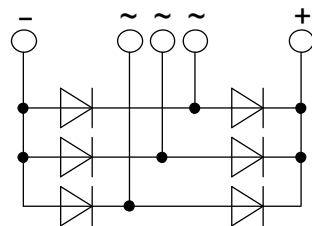
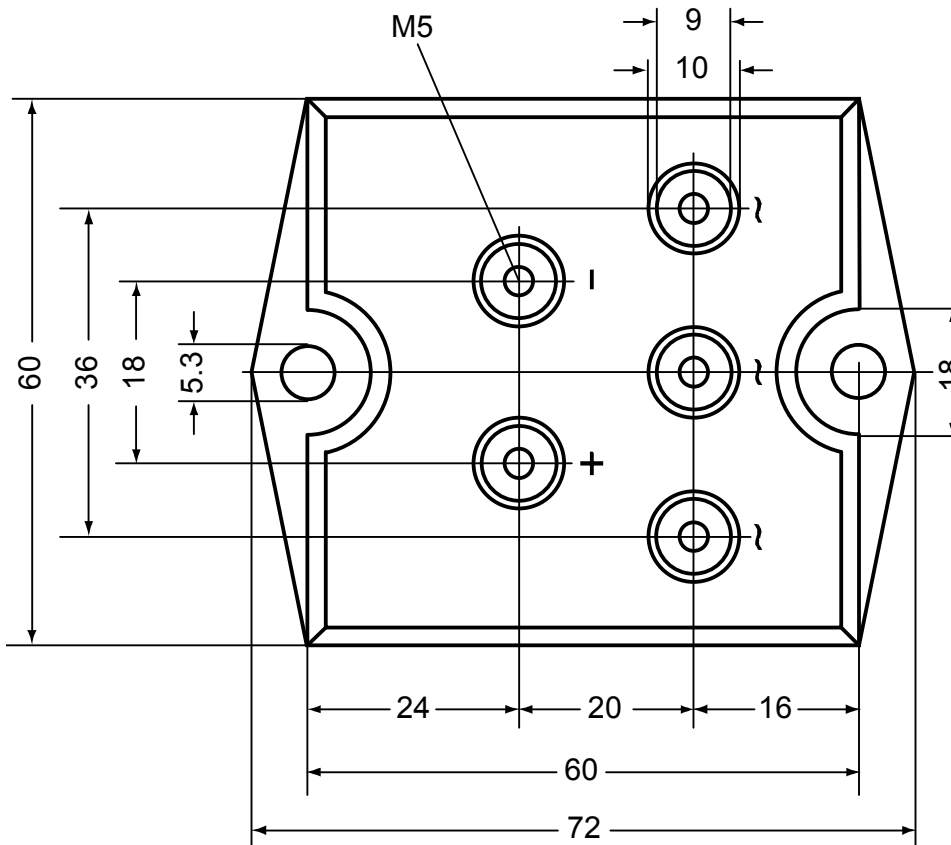
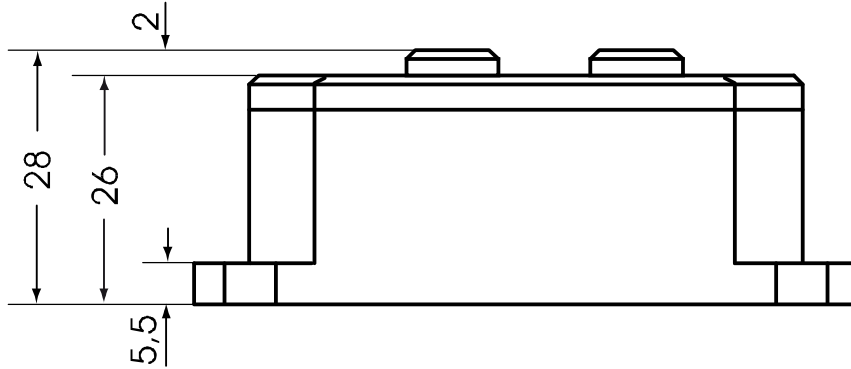
### Equivalent Circuits for Simulation

\* on die level

$T_{vj} = 150^\circ\text{C}$

Symbol	Definition	Value	Unit
$V_0$	threshold voltage	0.76	V
$R_0$	slope resistance *	5.7	mΩ

Outlines PWS-B



**Rectifier**

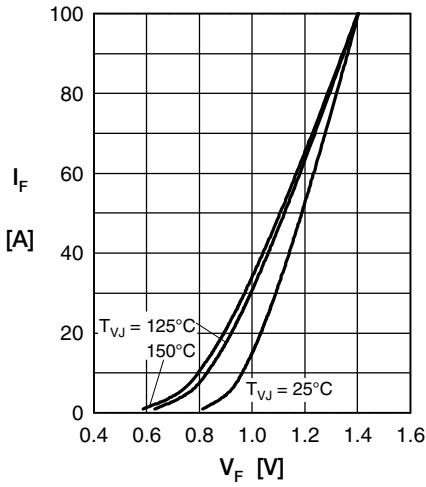


Fig. 1 Forward current vs. voltage drop per diode

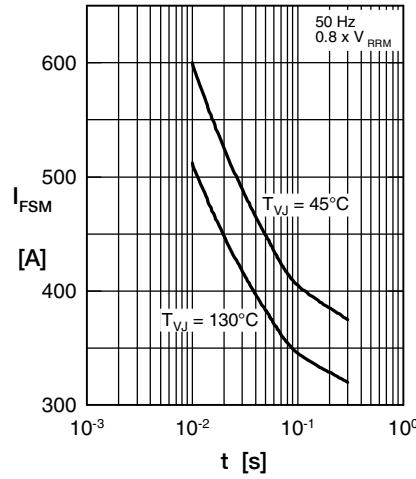


Fig. 2 Surge overload current vs. time per diode

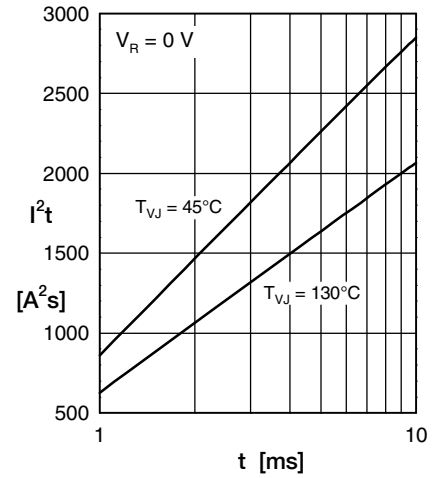


Fig. 3  $I^2t$  vs. time per diode

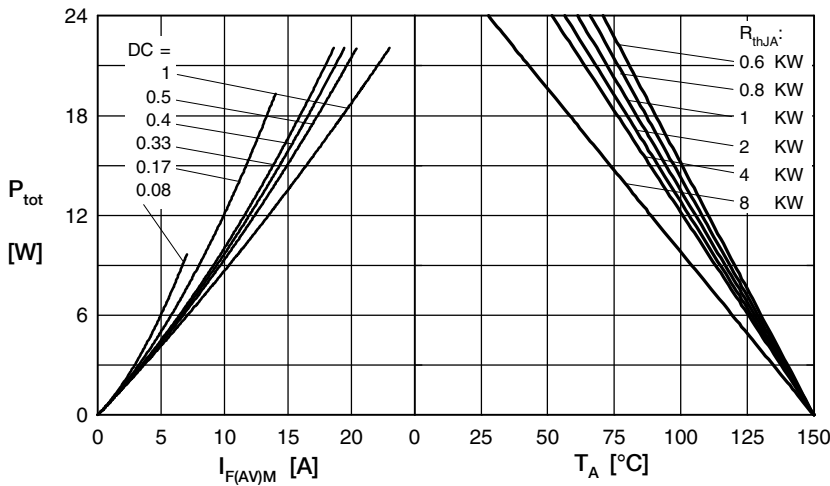


Fig. 4 Power dissipation vs. forward current and ambient temperature per diode

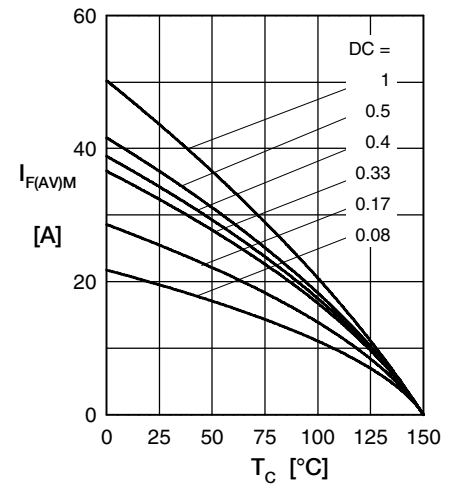


Fig. 5 Max. forward current vs. case temperature per diode

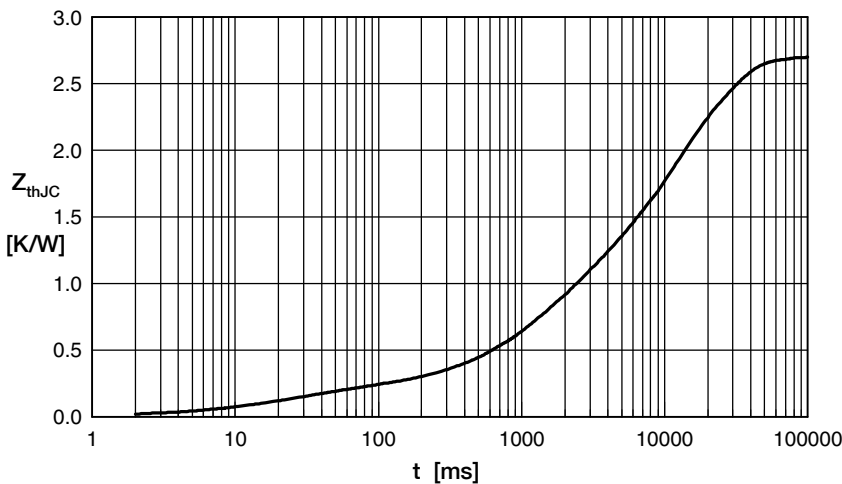


Fig. 6 Transient thermal impedance junction to case vs. time per diode

Constants for  $Z_{thJC}$  calculation:

i	$R_{th}$ (K/W)	$t_i$ (s)
1	0.040	0.010
2	0.150	0.030
3	0.610	1.350
4	1.900	14.00